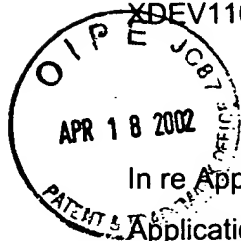


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PATENT
Customer ID: 25094



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
Application No.
Filing Date:
Group Art Unit:
Examiner:
Title:

Martin E. Kordesch et al.
09/682,151
July 27, 2001
2815
Chu, Chris C.

7/a
5-4-02
Payton

**CONTACT METHOD FOR THIN SILICON
CARBIDE EPITAXIAL LAYER AND
SEMICONDUCTOR DEVICES FORMED BY
THOSE METHODS**

Commissioner for Patents
Washington, D.C. 20231

Certification Under 37 C.F.R. § 1.8

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on April 10, 2002.

Carolyn J. Williams
Carolyn J. Williams

Dear Sir:

AMENDMENT

This Amendment is filed in regard to United States Patent Application No. 09/682,151 entitled "Contact Method for Thin Silicon Carbide Epitaxial Layer and Semiconductor Devices Formed by Those Methods" filed July 27, 2001. Please enter this Amendment into the current Application.

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IN THE SPECIFICATION:

Please insert the following paragraph on page 1 before "BACKGROUND OF INVENTION":

GOVERNMENTAL RIGHTS

a1
The U.S. Government has a paid-up license in this invention and the right in limited circumstances to require the patent owner to license others on reasonable terms as provided by the terms of F33615-01-C-1602 awarded by the Air Force Research Laboratory.